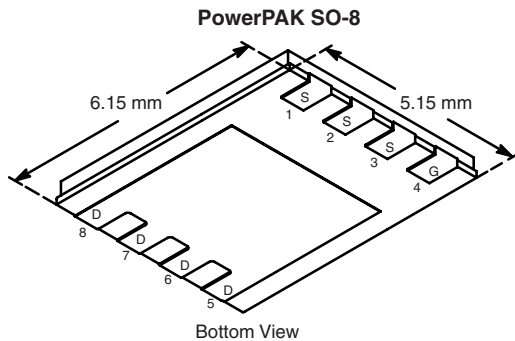




P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 20	0.0019 at V _{GS} = - 10 V	- 60 ^d	128 nC
	0.0030 at V _{GS} = - 4.5 V	- 60 ^d	



FEATURES

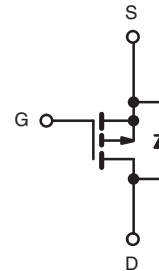
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Adaptor Switch
- Battery Switch
- Load Switch



Ordering Information: Si7141DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 20	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	- 60 ^d	A
	T _C = 70 °C		- 60 ^d	
	T _A = 25 °C		- 42.7 ^b	
	T _A = 70 °C		- 34 ^b	
Pulsed Drain Current		I _{DM}	- 100	
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 60 ^d	
	T _A = 25 °C		- 5.6 ^{a, b}	
Avalanche Current	L = 0.1 mH	I _{AS}	- 40	mJ
Single-Pulse Avalanche Energy		E _{AS}	80	
Maximum Power Dissipation	T _C = 25 °C	P _D	104	W
	T _C = 70 °C		66.6	
	T _A = 25 °C		6.25 ^{a, b}	
	T _A = 70 °C		4.0 ^{a, b}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{e, f}			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	t ≤ 10 s	R _{thJA}	15	20	°C/W
Maximum Junction-to-Case	Steady State	R _{thJC}	0.9	1.2	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 54 °C/W.
- Package limited.
- See Solder Profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 16		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			5.7		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.0		- 2.3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -10\text{ V}$	- 40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -25\text{ A}$		0.0015	0.0019	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		0.0024	0.0030	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -25\text{ A}$		103		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		14 300		pF
Output Capacitance	C_{oss}			2300		
Reverse Transfer Capacitance	C_{rss}			2600		
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		265	400	nC
				128	194	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		36		
Gate-Drain Charge	Q_{gd}			42		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.4	1.7	3.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 1\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		25	50	ns
Rise Time	t_r			16	30	
Turn-Off Delay Time	$t_{d(off)}$			130	220	
Fall Time	t_f			38	70	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 1\text{ }\Omega$ $I_D \equiv -10\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		130	220	
Rise Time	t_r			120	200	
Turn-Off Delay Time	$t_{d(off)}$			100	180	
Fall Time	t_f			55	100	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 60	A
Pulse Diode Forward Current	I_{SM}				- 100	
Body Diode Voltage	V_{SD}	$I_S = -5\text{ A}, V_{GS} = 0\text{ V}$		- 0.71	- 1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		42	80	ns
Body Diode Reverse Recovery Charge	Q_{rr}			36	72	nC
Reverse Recovery Fall Time	t_a			18		ns
Reverse Recovery Rise Time	t_b			24		

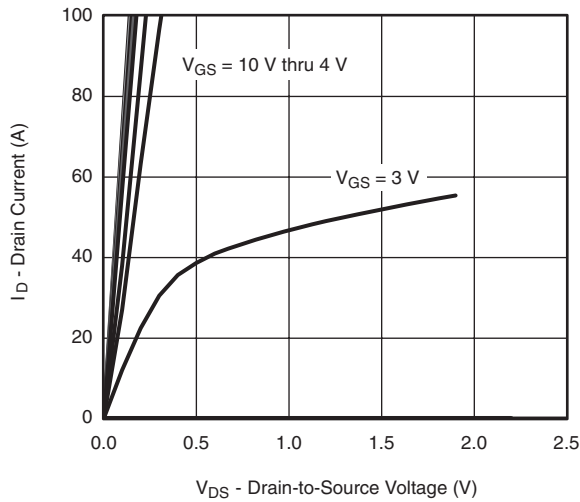
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

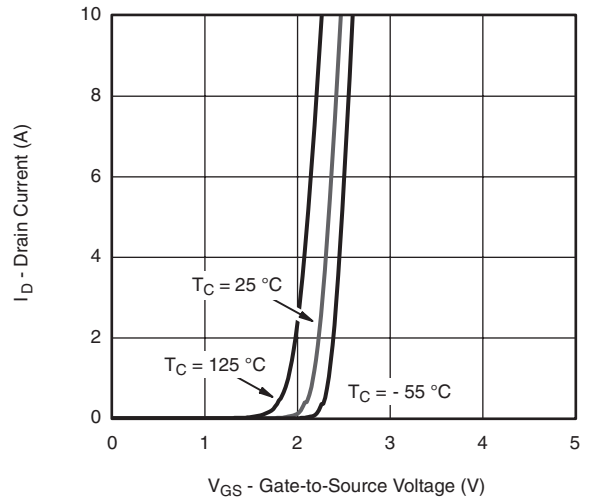
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



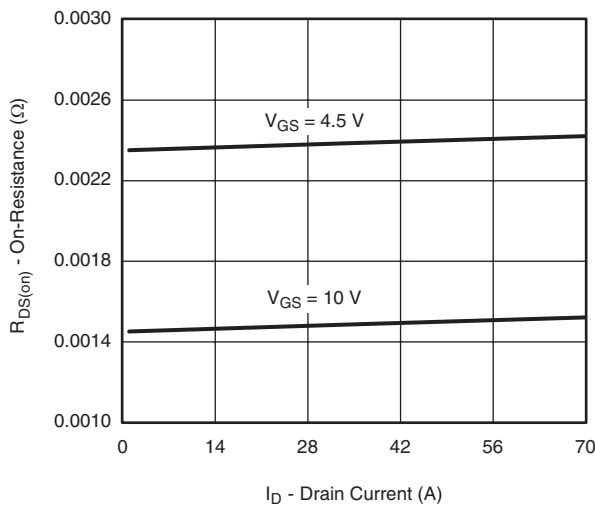
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



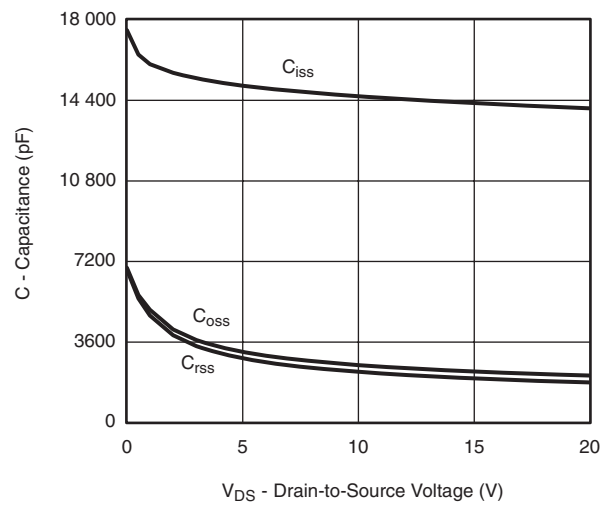
Output Characteristics



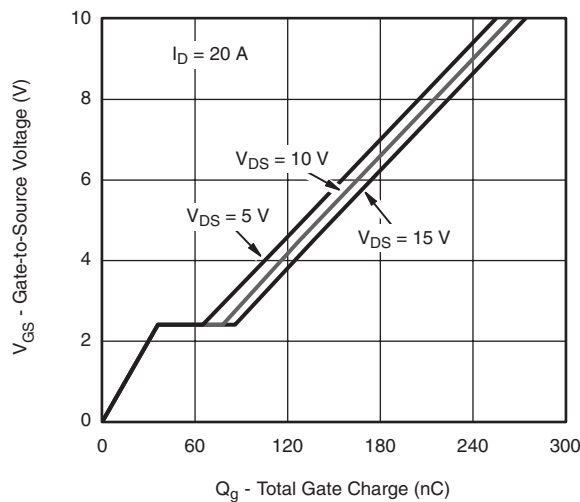
Transfer Characteristics



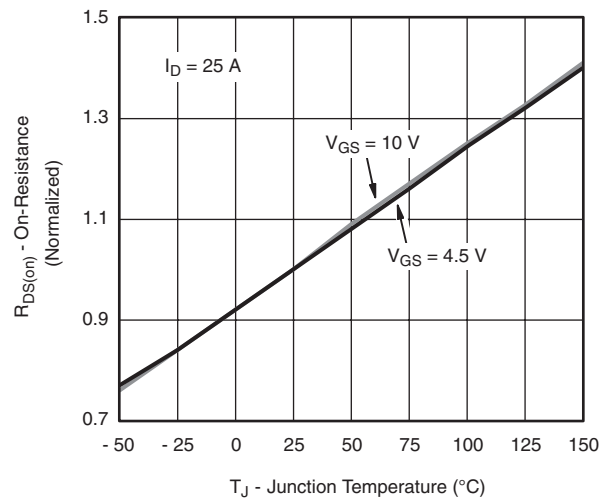
On-Resistance vs. Drain Current



Capacitance



Gate Charge



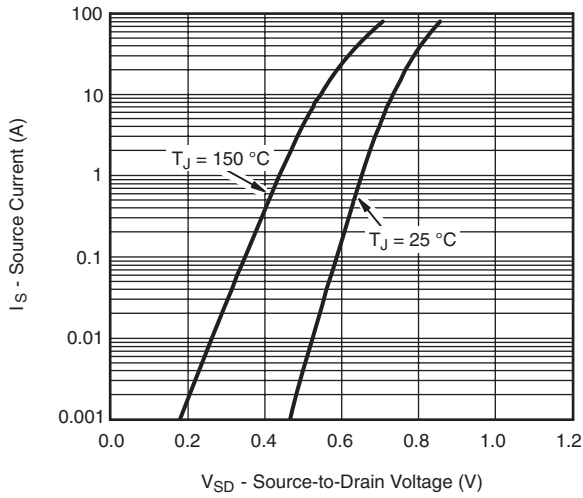
On-Resistance vs. Junction Temperature

Si7141DP

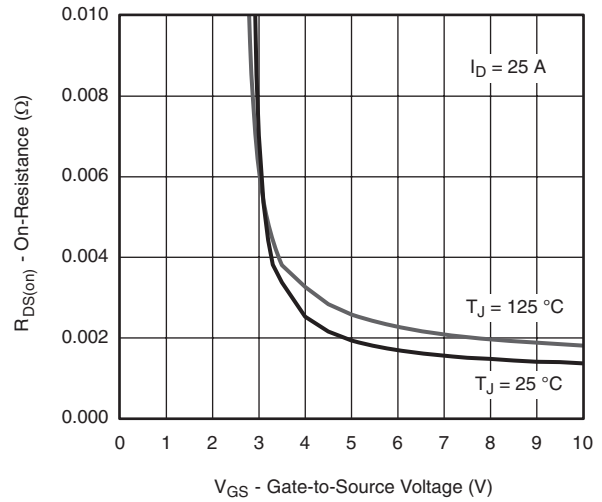
Vishay Siliconix



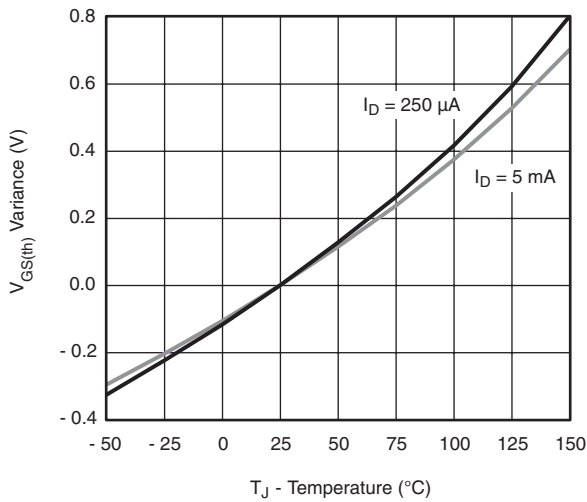
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



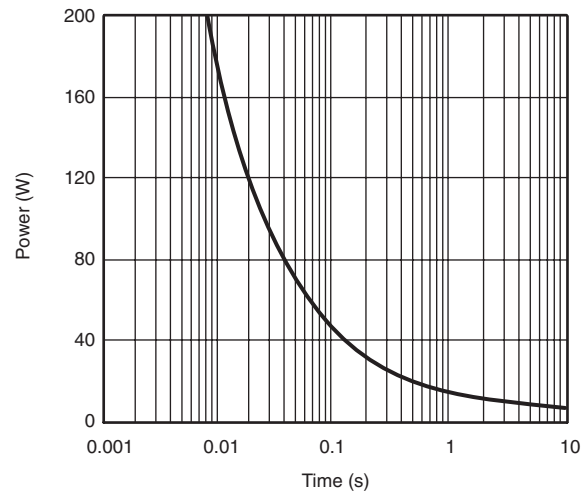
Source-Drain Diode Forward Voltage



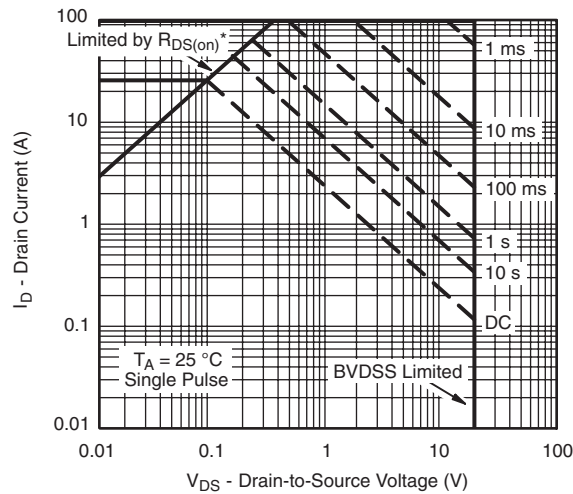
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

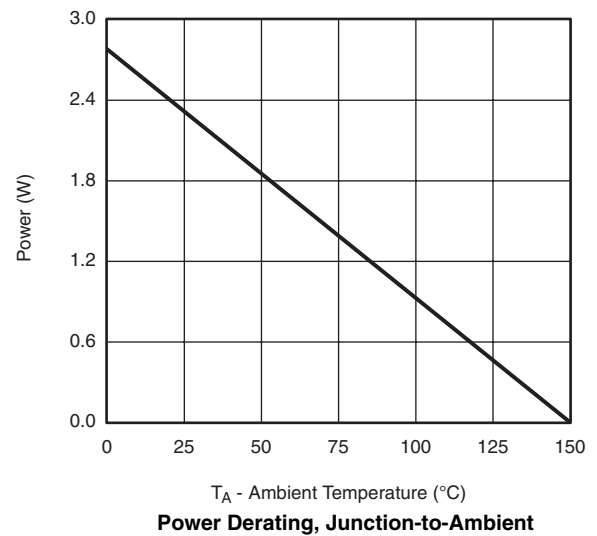
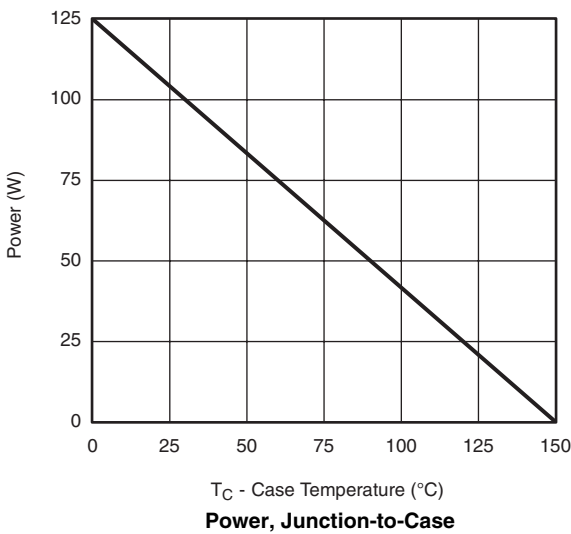
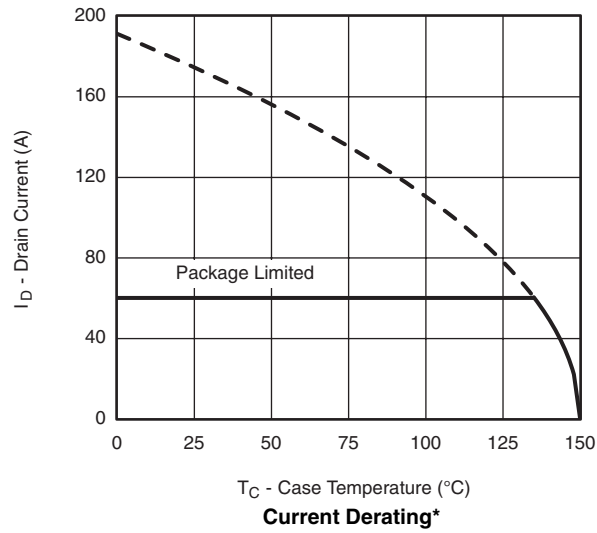


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



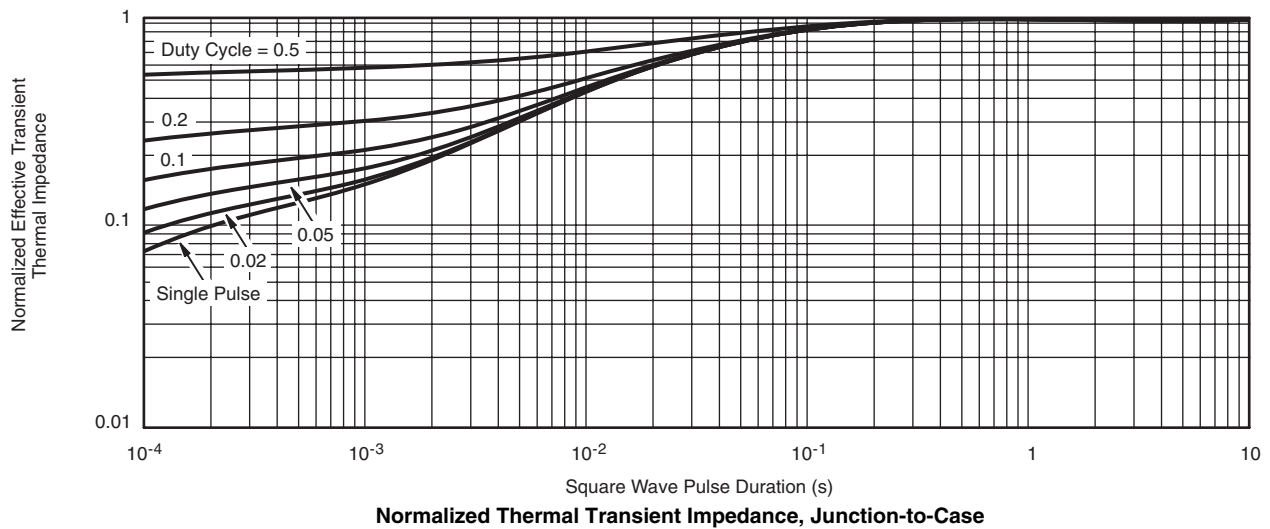
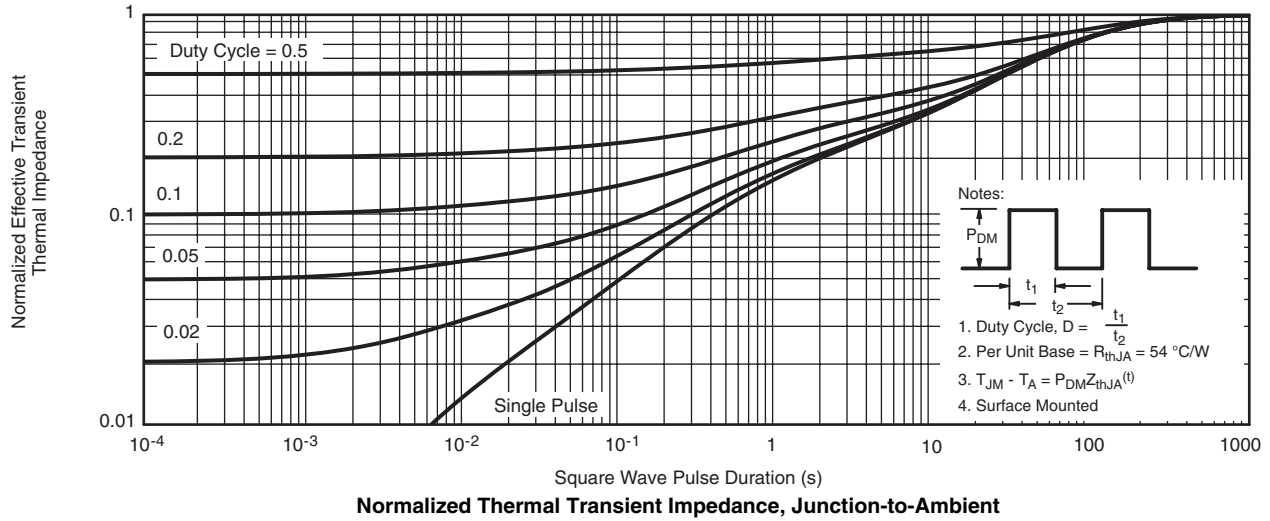
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si7141DP

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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